

N-channel MOS-FET			
250V	0,85Ω	6A	20W

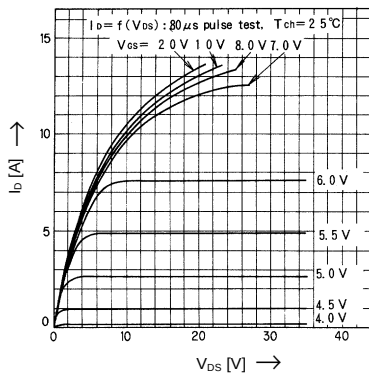
2SK2099-01L,S

FAP-IIA Series

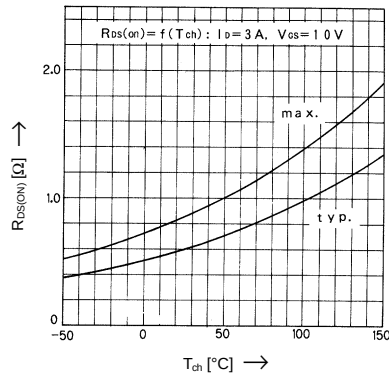
FUJI
ELECTRIC

> Characteristics

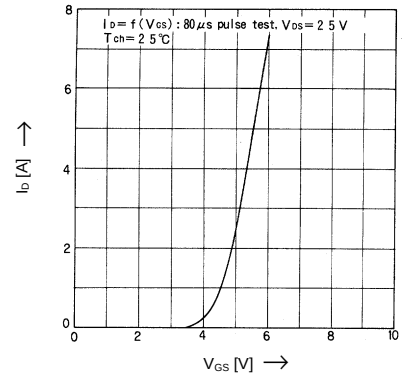
Typical Output Characteristics



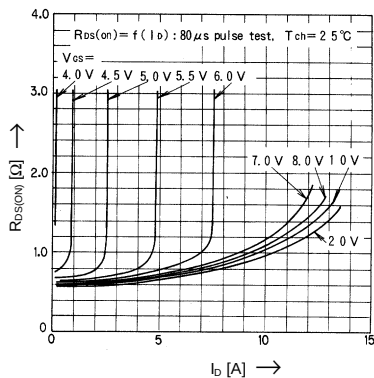
Drain-Source-On-State Resistance vs. Tch



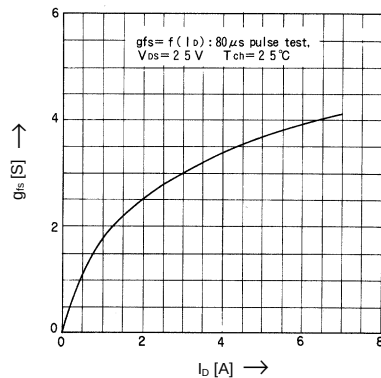
Typical Transfer Characteristics



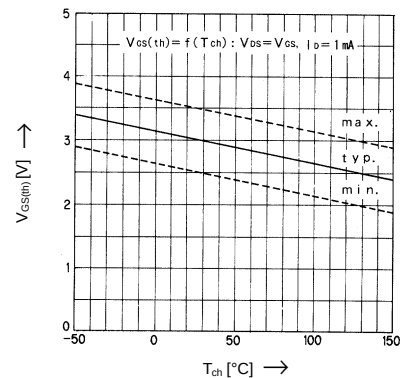
Typical Drain-Source-On-State-Resistance vs. Id



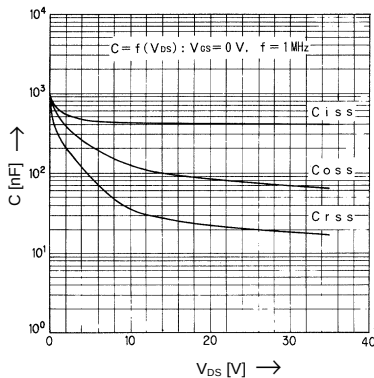
Typical Forward Transconductance vs. Id



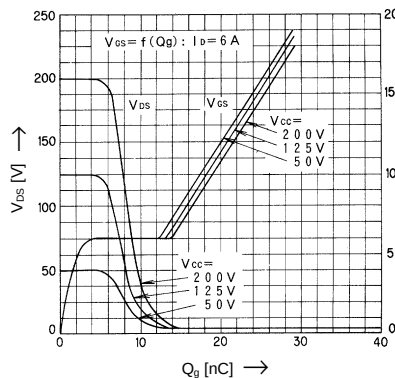
Gate Threshold Voltage vs. Tch



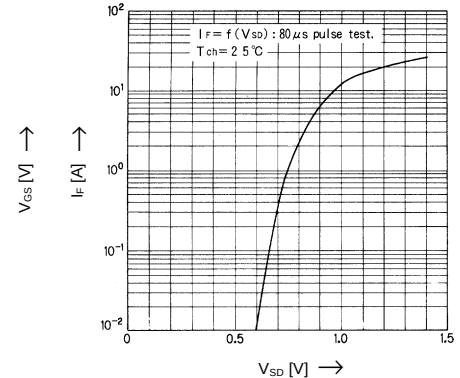
Typical Capacitance vs. Vds



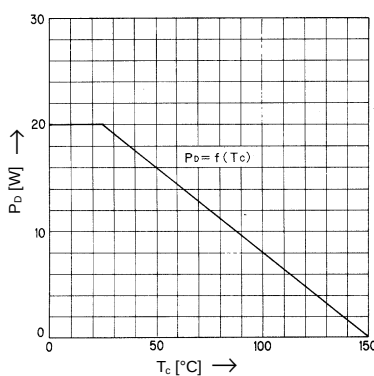
Typical Input Charge



Forward Characteristics of Reverse Diode



Allowable Power Dissipation vs. Tch



Safe operation area

